

Hiroyuki Yaguchi

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186
papers

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212
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2,559
ext. citations

1.8
avg, IF

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L-index

#	Paper	IF	Citations
186	Self-limitation in the surface segregation of Ge atoms during Si molecular beam epitaxial growth. <i>Applied Physics Letters</i> , 1991 , 59, 2103-2105	3.4	200
185	MOVPE growth of cubic GaN on GaAs using dimethylhydrazine. <i>Journal of Crystal Growth</i> , 1992 , 124, 439-442	1.6	134
184	Composition analysis of SiO ₂ /SiC interfaces by electron spectroscopic measurements using slope-shaped oxide films. <i>Applied Surface Science</i> , 2001 , 184, 161-166	6.7	98
183	Metalorganic vapor phase epitaxy of GaP _{1-x} N _x alloys on GaP. <i>Applied Physics Letters</i> , 1993 , 63, 3506-3508	3.4	86
182	Realization of Abrupt Interfaces in Si/Ge Superlattices by Suppressing Ge Surface Segregation with Submonolayer of Sb. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, L1981-L1983	1.4	86
181	Photoluminescence properties of cubic GaN grown on GaAs(100) substrates by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 1997 , 71, 2067-2069	3.4	71
180	Transmission Electron Microscope Observation of Cubic GaN Grown by Metalorganic Vapor Phase Epitaxy with Dimethylhydrazine on (001) GaAs. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 18-22	1.4	65
179	A Kinetic Model of Silicon Carbide Oxidation Based on the Interfacial Silicon and Carbon Emission Phenomenon. <i>Applied Physics Express</i> , 2009 , 2, 021203	2.4	64
178	Naturally formed ZnCdSe quantum dots on ZnSe (110) surfaces. <i>Applied Physics Letters</i> , 1997 , 70, 2413-2415	3.4	52
177	Photoluminescence excitation spectroscopy of GaP _{1-x} N _x alloys: conduction-band-edge formation by nitrogen incorporation. <i>Journal of Crystal Growth</i> , 1997 , 170, 353-356	1.6	47
176	Involvement of the topmost Ge layer in the Ge surface segregation during Si/Ge heterostructure formation. <i>Applied Physics Letters</i> , 1991 , 59, 2240-2241	3.4	46
175	Optical Constants of Cubic GaN, AlN, and AlGa _{1-x} N _x Alloys. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L497-L499	1.4	44
174	Oxide Growth Rate Enhancement of Silicon Carbide (0001) Si-Faces in Thin Oxide Regime. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 7803-7806	1.4	39
173	Crystal Structure of GaN Grown on 3C-SiC Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 4241-4245	1.4	37
172	MOVPE Growth and Luminescence Properties of GaAsN Alloys with Higher Nitrogen Concentrations. <i>Physica Status Solidi A</i> , 1999 , 176, 231-235		36
171	Sublattice Reversal in GaAs/Si/GaAs (100) Heterostructures by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, L1493-L1496	1.4	32
170	Metalorganic Vapor Phase Epitaxy Growth of High Quality Cubic GaN on GaAs (100) Substrates. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 1440-1442	1.4	31

169	Atomistic picture of interfacial mixing in the Si/Ge heterostructures. <i>Surface Science</i> , 1992 , 267, 79-82	1.8	30
168	Differences in SiC thermal oxidation process between crystalline surface orientations observed by in-situ spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 2015 , 117, 095306	2.5	29
167	Growth Rate Enhancement of (000bar1)-Face Silicon Carbide Oxidation in Thin Oxide Regime. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, L770-L772	1.4	29
166	Photoluminescence Study on Temperature Dependence of Band Gap Energy of GaAsN Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 228, 273-277	1.3	27
165	RHEED study of superstructures of submonolayer lead films on silicon (111) surfaces. <i>Applied Surface Science</i> , 1988 , 33-34, 75-80	6.7	27
164	Fabrication of Pb(Zr,Ti)O ₃ /MgO/GaN/GaAs structure for optoelectronic device applications. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 227-230	1.6	23
163	Characterization of Ge/SiGe strained-barrier quantum-well structures using photoreflectance spectroscopy. <i>Physical Review B</i> , 1994 , 49, 7394-7399	3.3	23
162	Intermediate range between N-doped GaP and GaP _{1-x} N _x alloys: difference in optical properties. <i>Journal of Crystal Growth</i> , 1994 , 145, 87-92	1.6	22
161	Oxygen partial pressure dependence of the SiC oxidation process studied by in-situ spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 2012 , 112, 024502	2.5	21
160	Nitrogen concentration dependence of photoluminescence decay time in GaP _{1-x} N _x alloys. <i>Solid-State Electronics</i> , 1997 , 41, 231-233	1.7	20
159	Characterization of Carrier Concentration and Mobility in n-type SiC Wafers Using Infrared Reflectance Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 5151-5156	1.4	20
158	The optical processes in AlInP/GaNP/AlInP quantum wells. <i>Journal of Applied Physics</i> , 1996 , 80, 4592-4598	2.5	20
157	Micro Raman and micro photoluminescence study of cubic GaN grown on 3C-SiC(001) substrates by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1998 , 195, 323-327	1.6	19
156	Effect of Ar post-oxidation annealing on oxide/H-SiC interfaces studied by capacitance to voltage measurements and photoemission spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005 , 23, 298-303	2.9	19
155	Intersubband absorption in narrow Si/SiGe multiple quantum wells without interfacial smearing. <i>Applied Physics Letters</i> , 1992 , 61, 210-212	3.4	19
154	RF-MBE growth of a-plane InN on r-plane sapphire with a GaN underlayer. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 517-520	1.6	18
153	Characterization of oxide films on 4H-SiC epitaxial (0001) faces by high-energy-resolution photoemission spectroscopy: Comparison between wet and dry oxidation. <i>Journal of Applied Physics</i> , 2006 , 100, 053710	2.5	18
152	Selective Growth of Cubic GaN in Small Areas on Patterned GaAs(100) Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 694-697	1.4	18

- 151 Is low temperature growth the solution to abrupt Si/Si_{1-x}Gex interface formation?. *Journal of Crystal Growth*, **1993**, 127, 401-405 1.6 18
- 150 RF-MBE growth of cubic InN films on MgO (001) substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1515-1518 17
- 149 Characterization of Oxide Films on SiC by Spectroscopic Ellipsometry. *Japanese Journal of Applied Physics*, **2000**, 39, L1054-L1056 1.4 17
- 148 Twin photoluminescence peaks from single isoelectronic traps in nitrogen doped GaAs. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 2110-2112 3 16
- 147 Epitaxial growth of hexagonal and cubic InN films. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 2839-2842 1.3 16
- 146 Photoreflectance Study of GaAs/GaAsP Strained-Barrier Quantum Well Structures. *Japanese Journal of Applied Physics*, **1993**, 32, 544-547 1.4 16
- 145 Simultaneous Determination of Carrier Concentration, Mobility, and Thickness of SiC Homoepilayers by Infrared Reflectance Spectroscopy. *Japanese Journal of Applied Physics*, **2006**, 45, L1226-L1229 1.4 15
- 144 Measurements of the Depth Profile of the Refractive Indices in Oxide Films on SiC by Spectroscopic Ellipsometry. *Japanese Journal of Applied Physics*, **2002**, 41, 800-804 1.4 15
- 143 Kinetics of Ge Segregation in the Presence of Sb During Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1991**, 220, 217 15
- 142 Cleaved cavity stimulated emission from an optically pumped cubic GaN/AlGaIn heterostructure grown on GaAs (100) substrate. *Applied Physics Letters*, **1998**, 73, 1931-1933 3.4 14
- 141 Optical and electrical characterizations of 4H-SiC/oxide interfaces by spectroscopic ellipsometry and capacitance-voltage measurements. *Applied Surface Science*, **2009**, 255, 8648-8653 6.7 13
- 140 Photoluminescence and photoluminescence-excitation spectroscopy of GaPAsN/GaP lattice-matched multiple quantum well structures. *Journal of Crystal Growth*, **1998**, 195, 574-578 1.6 13
- 139 A new approach to ZnCdSe quantum dots. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1998**, 51, 127-131 3.1 13
- 138 Metalorganic vapor phase epitaxy growth and photoluminescence properties of cubic Al_xGa_{1-x}N. *Applied Physics Letters*, **1998**, 73, 193-195 3.4 13
- 137 Surface orientation dependence of growth rate of cubic GaN. *Journal of Crystal Growth*, **1994**, 145, 197-202 13
- 136 Photoluminescence from single isoelectronic traps in nitrogen delta-doped GaAs grown on GaAs(111)A. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 2529-2531 3 12
- 135 Real Time Observation of SiC Oxidation Using an In Situ Ellipsometer. *Materials Science Forum*, **2006**, 527-529, 1031-1034 0.4 12
- 134 Polarization Characteristics of Crescent-Shaped Tensile-Strained GaAsP/AlGaAs Quantum Wire-Like Lasers. *Japanese Journal of Applied Physics*, **1998**, 37, 1556-1558 1.4 12

133	Composition profile of an AlGaAs epilayer on a V-grooved substrate grown by low-pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 1995 , 67, 959-961	3.4	12
132	Temperature dependence of photoluminescence of GaP _{1-x} N _x alloys. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 496-499	1.6	11
131	Micro-photoluminescence study of nitrogen delta-doped GaAs grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 298, 73-75	1.6	11
130	Photoluminescence of cubic InN films on MgO (001) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1579-1581		11
129	Formation of Cubic GaN on (111)B GaAs by Metal-Organic Vapor-Phase Epitaxy with Dimethylhydrazine. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 3415-3416	1.4	11
128	Investigation of luminescence properties of GaN single crystals grown on 3C-SiC substrates. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 420-424	1.6	10
127	Improvement of the surface morphology of a -plane InN using low-temperature InN buffer layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1808-1810		10
126	Modulation spectroscopic investigation on lattice polarity of gallium nitride. <i>Applied Physics Letters</i> , 2007 , 91, 061917	3.4	10
125	Growth of high-quality hexagonal InN on 3C-SiC (001) by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2267-2270		10
124	Spatial Mapping of the Carrier Concentration and Mobility in SiC Wafers by Micro Fourier-Transform Infrared Spectroscopy. <i>Materials Science Forum</i> , 2002 , 389-393, 621-624	0.4	10
123	Optical characterization of metalorganic vapor-phase epitaxy-grown GaAs _{1-x} N _x alloys using spectroscopic ellipsometry. <i>Journal of Crystal Growth</i> , 2000 , 221, 481-484	1.6	10
122	Selective Growth of Cubic GaN on Patterned GaAs(100) Substrates by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 1999 , 176, 557-560		10
121	Theoretical Studies for Si and C Emission into SiC Layer during Oxidation. <i>Materials Science Forum</i> , 2011 , 679-680, 429-432	0.4	9
120	A highly luminescent crescent-shaped tensile-strained quantum wire laser structure. <i>Journal of Crystal Growth</i> , 1997 , 170, 585-589	1.6	9
119	Spectroscopic ellipsometry study on the dielectric functions of GaPN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2753-2756		9
118	Stimulated emission from optically pumped cubic GaN/AlGaIn double heterostructures. <i>Journal of Crystal Growth</i> , 1999 , 197, 73-77	1.6	9
117	Optical Characterization of Cubic AlGaIn Epilayers by Cathodoluminescence and Spectroscopic Ellipsometry. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 211-214	1.3	9
116	Metal-Organic Vapor Phase Epitaxy Growth and Optical Study of GaAs/GaAs _{1-x} P _x Strained-Barrier Single Quantum Well Structures. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, L375-L378	1.4	9

115	Strain Relaxation in MBE-Grown Si _{1-x} Ge _x /Si(100) Heterostructures by Annealing. <i>Japanese Journal of Applied Physics</i> , 1991 , 30, L1450-L1453	1.4	9
114	Enhanced optical absorption due to E ⁺ -related band transition in GaAs:N doped superlattices. <i>Applied Physics Express</i> , 2014 , 7, 102301	2.4	8
113	Characterization of 4H-SiC/BiO ₂ Interfaces by a Deep Ultraviolet Spectroscopic Ellipsometer. <i>Materials Science Forum</i> , 2009 , 615-617, 505-508	0.4	8
112	Biexciton Luminescence from Individual Isoelectronic Traps in Nitrogen δ -Doped GaAs. <i>Applied Physics Express</i> , 2012 , 5, 111201	2.4	8
111	Metalorganic Vapor Phase Epitaxy Growth Features of AlGaAs in Tetrahedral-Shaped Recesses on GaAs (111)B Substrates. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 4102-4106	1.4	8
110	Optical transitions in cubic GaN grown on GaAs(1 0 0) substrates by metalorganic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 415-419	1.6	8
109	Oxygen-Partial-Pressure Dependence of SiC Oxidation Rate Studied by In Situ Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , 2008 , 600-603, 667-670	0.4	8
108	Temperature Dependence of Excitonic π -Transition Energies of GaIn _{1-x} P Crystals. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 1183-1187	1.4	8
107	Second-Harmonic Generation from GaP/AlP Multilayers on GaP (111) Substrates Based on Quasi-Phase Matching for the Fundamental Standing Wave. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L334-L336	1.4	8
106	Self-modulating Sb incorporation in Si/SiGe superlattices during molecular beam epitaxial growth. <i>Surface Science</i> , 1993 , 295, 335-339	1.8	8
105	Direct Evidence of Carrier Excitation from Intermediate Band States in GaPN by Two-Wavelength Excited Photoluminescence. <i>Applied Physics Express</i> , 2013 , 6, 092401	2.4	7
104	Metalorganic vapor-phase epitaxy of GaP _{1-x} As _y N _x quaternary alloys on GaP. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 485-489	1.6	7
103	Model Calculation of SiC Oxidation Rates in the Thin Oxide Regime. <i>Materials Science Forum</i> , 2008 , 600-603, 663-666	0.4	7
102	RF-MBE growth of InN/InGaN quantum well structures on 3C-SiC substrates. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 513-516	1.6	7
101	Control of Macroscopic Absorption Coefficient of Multicrystalline SiGe by Microscopic Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L37-L39	1.4	7
100	Substrate Misorientation Dependence of the Hexagonal Phase Inclusion in Cubic GaN Films Grown by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 1999 , 176, 513-517		7
99	Evolution of morphology and crystalline quality of DC-sputtered AlN films with high-temperature annealing. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC1029	1.4	6
98	Analysis of Electronic Structures of Nitrogen doped GaAs Superlattices for High Efficiency Intermediate Band Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2013 , 3, 1287-1291	3.7	6

97	Spectral change of intermediate band luminescence in GaP:N due to below-gap excitation: Discrimination from thermal activation. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600566	1.3	6
96	Photoluminescence study of oxidation-induced faults in 4H-SiC epilayers. <i>AIP Advances</i> , 2015 , 5, 127116	1.5	6
95	Microstructures of InN film on 4H-SiC (0001) substrate grown by RF-MBE. <i>Journal of Semiconductors</i> , 2015 , 36, 083002	2.3	6
94	Thermal Oxidation Mechanism of Silicon Carbide 2012 ,		6
93	Conversion Efficiency of Intermediate Band Solar Cells with GaAs:N δ -Doped Superlattices. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 102302	1.4	6
92	Quantum well double barrier resonant tunneling structures for selective contacts of hot carrier solar cells 2011 ,		6
91	Model Calculation of SiC Oxide Growth Rate Based on the Silicon and Carbon Emission Model. <i>Materials Science Forum</i> , 2009 , 615-617, 489-492	0.4	6
90	The δ -Transition Energies of $\text{Al}_x\text{In}_{1-x}\text{P}$ Alloys. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 6607-6613	1.4	6
89	Time-Resolved Photoluminescence of Cubic GaN Grown by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 237-240	1.3	6
88	Observation of the valence-subband level crossing in GaAs/GaAsP strained-barrier quantum well structures using circularly polarized photoluminescence excitation spectroscopy. <i>Applied Physics Letters</i> , 1993 , 63, 946-948	3.4	6
87	Intersubband absorption in n-type Si/Si $_{1-x}$ Ge $_x$ multiple quantum well structures formed by Sb segregant-assisted growth. <i>Journal of Crystal Growth</i> , 1993 , 127, 416-420	1.6	6
86	Control of intermediate-band configuration in GaAs:N δ -doped superlattice. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA04	1.4	5
85	RF-MBE growth of cubic InN nano-scale dots on cubic GaN. <i>Journal of Crystal Growth</i> , 2013 , 378, 454-458	1.6	5
84	Self-organized growth of cubic InN dot arrays on cubic GaN using MgO (001) vicinal substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600542	1.3	5
83	Influence of off-cut angle of (0001) 4H-SiC on the crystal quality of InN grown by RF-MBE. <i>Procedia Engineering</i> , 2012 , 32, 882-887		5
82	OPTICAL PROPERTIES AND CARRIER DYNAMICS IN ASYMMETRIC COUPLED InGaN MULTIPLE QUANTUM WELLS. <i>Functional Materials Letters</i> , 2013 , 06, 1350021	1.2	5
81	Model Calculations of SiC Oxide Growth Rate at Various Oxidation Temperatures Based on the Silicon and Carbon Emission Model. <i>Materials Science Forum</i> , 2010 , 645-648, 809-812	0.4	5
80	Theoretical study of conduction band edge formation in GaP $_{1-x}$ N $_x$ alloys using a tight-binding approximation. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 500-504	1.6	5

79	Photoluminescence study of isoelectronic traps in dilute GaAsN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2760-2763		5
78	Tensile-strained GaAsP/AlGaAs quantum wells grown by low-pressure metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 1995 , 78, 3517-3519	2.5	5
77	Growth temperature dependence of AlGaAs spontaneous vertical quantum wells on V-grooved substrates by low-pressure metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1996 , 158, 205-209	1.6	5
76	Metalorganic vapor phase epitaxial growth and luminescence properties of GaAs/GaAsP quantum wires. <i>Journal of Crystal Growth</i> , 1994 , 145, 702-706	1.6	5
75	Epitaxial growth of CH ₃ NH ₃ PbI ₃ on rubrene single crystal. <i>APL Materials</i> , 2020 , 8, 041104	5.7	4
74	RF-MBE growth of cubic AlN on MgO (001) substrates via 2-step c-GaN buffer layer. <i>Journal of Crystal Growth</i> , 2013 , 378, 307-309	1.6	4
73	Growth of InN/GaN dots on 4H-SiC(0001) off vicinal substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017 , 477, 201-206	1.6	4
72	Molecular beam epitaxial growth of intermediate-band materials based on GaAs:N doped superlattices. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA07	1.4	4
71	Photoreflectance study of the temperature dependence of excitonic transitions in dilute GaAsN alloys. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 752-755	1.6	4
70	Observation of optical spin injection into Ge-based structures at room temperature. <i>Applied Physics Letters</i> , 2013 , 102, 242104	3.4	4
69	Growth Mechanism in the Metalorganic Vapor Phase Epitaxy of Metastable GaP _{1-x} N _x Alloys: A Growth Interruption Study. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 7110-7118	1.4	4
68	Characterization of Electrical Properties in High-Dose Implanted and Post-Implantation-Annealed 4H-SiC Wafers using Infrared Reflectance Spectroscopy. <i>Materials Science Forum</i> , 2004 , 457-460, 905-908	0.4	4
67	Improvement in the luminescence efficiency of GaAsN alloys by photoexcitation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2782-2784		4
66	X-Ray Photoelectron Spectroscopy Studies of Post-Oxidation Process Effects on Oxide/SiC Interfaces. <i>Materials Science Forum</i> , 2002 , 389-393, 1033-1036	0.4	4
65	Rectangular AlGaAs/AlAs Quantum Wires Using Spontaneous Vertical Quantum Wells. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 1214-1216	1.4	4
64	Photoluminescence study of (111)-oriented GaAs/GaAsP strained-layer quantum well structure. <i>Applied Physics Letters</i> , 1994 , 64, 1555-1557	3.4	4
63	Suppression of Interfacial Mixing by Sb Deposition in Si/Ge Strained-Layer Superlattices. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 220, 193		4
62	Nonradiative recombination centers in GaAs:N doped superlattice revealed by two-wavelength-excited photoluminescence. <i>Journal of Applied Physics</i> , 2018 , 123, 161426	2.5	3

61	First-principles study on the conduction band electron states of GaAsN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 911-913		3
60	Si Emission into the Oxide Layer during Oxidation of Silicon Carbide. <i>Materials Science Forum</i> , 2014 , 778-780, 553-556	0.4	3
59	Model Calculations of SiC Oxide Growth Rates at Sub-Atmospheric Pressures Using the Si and C Emission Model. <i>Materials Science Forum</i> , 2013 , 740-742, 833-836	0.4	3
58	Stacked structure of self-organized cubic InN nano-dots grown by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1545-1548		3
57	High Cubic-Phase Purity InN on MgO (001) Using Cubic-Phase GaN as a Buffer Layer 2011 ,		3
56	Single photon emission from nitrogen delta-doped semiconductors 2011 ,		3
55	MOVPE Growth of GaPAsN Quaternary Alloys Lattice-Matched to GaP. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 482, 259		3
54	Electronic structure of strained-layer quantum wells. <i>Surface Science</i> , 1997 , 387, 371-382	1.8	3
53	Self-assembled, very long III-V semiconductor quantum wires. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1998 , 51, 224-228	3.1	3
52	Off-Angle Dependence of Characteristics of 4H-SiC-Oxide Interfaces. <i>Materials Science Forum</i> , 2006 , 527-529, 1003-1006	0.4	3
51	Characterization of Oxide Films on SiC Epitaxial (000-1) Faces by Angle-Resolved Photoemission Spectroscopy Measurements Using Synchrotron Radiation. <i>Materials Science Forum</i> , 2005 , 483-485, 585-588	0.4	3
50	Characterization of the Interfaces between SiC and Oxide Films by Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , 2002 , 389-393, 1029-1032	0.4	3
49	Fabrication and optical properties of GaAs/AlGaAs quantum dot grown in tetrahedral-shaped recesses on GaAs B substrates by MOVPE. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 308-316	3	3
48	GaAs/AlGaAs Quantum Structures Grown in Tetrahedral-Shaped Recesses on GaAs (111)B Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 1493-1496	1.4	3
47	High-Temperature Metalorganic Vapor Phase Epitaxial Growth of GaAs/AlGaAs Quantum Structures in Tetrahedral-Shaped Recesses on GaAs (111)B Substrates. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 459-464	1.4	3
46	Optical property of GaAsP/AlGaAs strained-layer quantum well grown on GaAs-(111)B substrate. <i>Applied Physics Letters</i> , 1995 , 66, 186-188	3.4	3
45	Effects of solvent vapor annealing on organic photovoltaics with a new type of solution-processable oligothiophene-based electronic donor material. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RE09	1.4	3
44	Growth temperature dependence of cubic GaN step structures and cubic InN dot arrays grown on MgO (001) vicinal substrates. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC1051	1.4	2

43	Nondestructive and Contactless Characterization Method for Spatial Mapping of the Thickness and Electrical Properties in Homo-Epitaxially Grown SiC Epilayers Using Infrared Reflectance Spectroscopy 2012 ,		2
42	RF-MBE growth of semipolar InN(10-13) and InGaN(10-13) on GaAs(110). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 658-661		2
41	In Situ Spectroscopic Ellipsometry Study of SiC Oxidation at Low Oxygen-Partial-Pressures. <i>Materials Science Forum</i> , 2010 , 645-648, 813-816	0.4	2
40	Observation of SiC Oxidation in Ultra-Thin Oxide Regime by In Situ Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , 2009 , 615-617, 509-512	0.4	2
39	Single Photon Generation from Nitrogen Atomic-Layer Doped Gallium Arsenide. <i>Materials Science Forum</i> , 2012 , 706-709, 2916-2921	0.4	2
38	Micro-Photoluminescence Study on the Influence of Oxidation on Stacking Faults in 4H-SiC Epilayers. <i>Applied Physics Express</i> , 2012 , 5, 051302	2.4	2
37	RF-MBE growth of InN on 4H-SiC (0001) with off-angles. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2016-2018		2
36	Self Formation and Optical Properties of II-VI Semiconductor Wire Structures. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, L1490-L1493	1.4	2
35	Characterization of SiGe strained heterostructures grown by molecular beam epitaxy using a Si effusion cell. <i>Thin Solid Films</i> , 1998 , 321, 241-244	2.2	2
34	Micro-Raman study on the improvement of luminescence efficiency of GaAsN alloys. <i>Journal of Crystal Growth</i> , 2007 , 298, 131-134	1.6	2
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30	Spectroscopic Ellipsometry Study on the Electronic Structure near the Absorption Edge of GaAsN Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 228, 269-272	1.3	2
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28	Arsenic Surfactant and Incorporation Effects on Cubic GaN Grown by Metalorganic Vapor Phase Epitaxy 1999 ,		2
27	RHEED study of Pb/Si(111) surface superstructures.. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 1988 , 31, 399-401		2
26	Detection of Nonradiative Recombination Centers in GaPN (N:0.105%) by Below-Gap Excitation Light. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900377	1.3	2

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23	Surface Orientation Dependence of SiC Oxidation Process Studied by In Situ Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , 2015 , 821-823, 371-374	0.4	1
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20	Photoluminescence study of hexagonal InN/InGaN quantum well structures grown on 3C-SiC (001) substrates by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1730-1732		1
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